



OCTAL TRANSPARENT D-TYPE LATCH WITH 3 STATE OUTPUTS

Description

The 74LVC573A provides eight transparent D-type latches. While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs. A buffered output-enable $\overline{(OE)}$ input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components. \overline{OE} does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

These devices feature inputs and outputs on opposite sides of the package that facilitate printed circuit board layout. The device is designed for operation with a power supply range of 1.65V to 3.6V.

The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down.

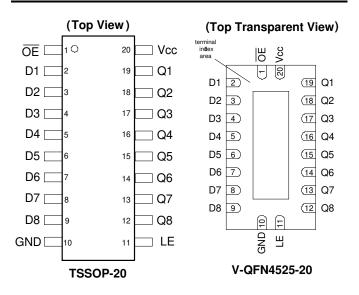
Features

- Supply Voltage Range from 1.65V to 3.6V
- Sinks or Sources 24mA at V_{CC} = 3V
- CMOS Low Power Consumption
- I_{OFF} Supports Partial-Power Down Operation
- Inputs or Outputs Accept Up to 5.5V
- Inputs Can Be Driven by 3.3V or 5V Allowing for Mixed Voltage Applications
- Schmitt Trigger Action at All Inputs
- Typical V_{OLP} (Quiet Output Ground Bounce) Less than 0.8V with V_{CC} = 3.3V and T_A = +25°C
- Typical V_{OHV} (Quiet Output Dynamic VOH) Greater than 2.0V with V_{CC} = 3.3V and T_A = +25°C
- ESD Protection Tested per JESD 22
 - Exceeds 200-V Machine Model (A115)
 - Exceeds 2000-V Human Body Model (A114)
 - Exceeds 1000-V Charged Device Model (C101)
- Latch-Up Exceeds 250mA per JESD 78, Class I
- All devices are:
 - Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
 - Halogen and Antimony Free. "Green" Device (Note 3)

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Assignments

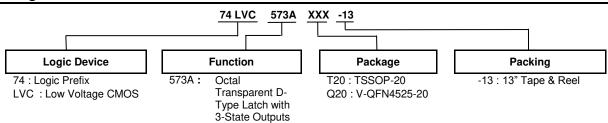


Applications

- General Purpose Logic
- Bus Driving
- Power Down Signal Isolation
 - Wide Array of Products such as:
 - PCs, Notebooks, Netbooks, Ultrabooks
 - Networking Computer Peripherals, Hard Drives, CD/DVD ROM
 - TV, DVD, DVR, Set Top Box



Ordering Information



Part Number	Package	Package	Package	13" Tape and I	Reel
Part Number	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix
74LVC573AT20-13	T20	TSSOP-20	6.4mm X 6.5mm X 1.2mm 0.65mm Lead Pitch	2500/Tape & Reel	-13
74LVC573AQ20-13	Q20	V-QFN4525-20	2.5mm X 4.5mm X 0.95mm 0.50mm Lead Pitch	2500/Tape & Reel	-13

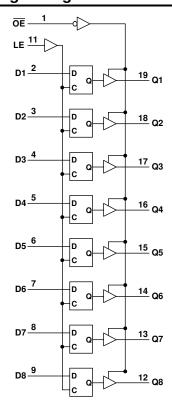
Notes:

4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
5. V-QFN4525-20 is a JEDEC recognized naming convention that specifies the package thickness category as V and the number 4525 describes the package as 4.5mm X 2.5mm.

Pin Descriptions

Di-	D:	
Pin Number	Pin Name	Description
1	OE	Output Enable
2	D1	Data Input
3	D2	Data Input
4	D3	Data Input
5	D4	Data Input
6	D5	Data Input
7	D6	Data Input
8	D7	Data Input
9	D8	Data Input
10	GND	Ground
11	LE	Latch Enable
12	Q8	Latch Output
13	Q7	Latch Output
14	Q6	Latch Output
15	Q5	Latch Output
16	Q4	Latch Output
17	Q3	Latch Output
18	Q2	Latch Output
19	Q1	Latch Output
20	Vcc	Supply Voltage

Logic Diagram



Function Table

(Each Latch)							
	INPUTS		OUTPUT				
OE	LE	D	Q				
L	Н	Н	Н				
L	Н	L	L				
L	L	Х	Q_0				
Н	Χ	Χ	Z				



Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V_{CC}	Supply Voltage Range	-0.5 to +7.0	V
VI	Input Voltage Range	-0.5 to +7.0	V
I _{IK}	Input Clamp Current V _I < 0V	-20	mA
I _{OK}	Output Clamp Current V _O < 0V	-50	mA
Io	Continuous Output Current -0.5V < V _O V _{CC} +0.5V	±50	mA
Icc	Continuous Current Through V _{CC}	100	mA
I _{GND}	Continuous Current Through GND	-100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C
P _{TOT}	Total Power Dissipation	500	mW

Notes:

- 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be
- within recommend values.

 7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8)

Symbol	Parameter	Conditions	Min	Max	Unit	
	Cumply Voltage	Operating	1.65	3.6	V	
V _{CC}	Supply Voltage	Data Retention Only	1.5	_	V	
VI	Input Voltage	_	0	5.5	V	
Vo	Output Voltage	_	0	V _{CC}	V	
		V _{CC} = 1.65V	_	-4		
	High-Level Output Current	V _{CC} = 2.3V	_	-8		
Іон		V _{CC} = 2.7V	_	-12	mA	
		V _{CC} = 3.0V	_	-24		
		V _{CC} = 1.65V	_	4		
	Lave Lavel Cutavt Cumant	V _{CC} = 2.3V	_	8	A	
I _{OL}	Low-Level Output Current	V _{CC} = 2.7V	_	12	mA	
		V _{CC} = 3.0V	_	24		
Δt/ΔV	Input Transition Rise or Fall Rate	_	_	10	ns/V	
TA	Operating Free-Air Temperature	_	-40	+125	°C	

Note:

8. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics

Symbol	Parameter	Too! C	onditions	V	T _A = -40°C	c to +85°C	T _A = -40°C	to +125°C	Unit
Symbol	Test Conditions	Vcc	Min	Max	Min	Max	Unit		
		_		1.65V to 1.95V	V _{CC} X 0.65	_	V _{CC} X 0.65	_	
V_{IH}	High-Level Input Voltage	_		2.3V to 2.7V	1.7	_	1.7	_	V
	Voltage	_		3.0V to 3.6V	2		2	_	
	Lave Lavel Innex	_		1.65V to 1.95V	_	V _{CC} X 0.35	_	V _{CC} X 0.35	
V_{IL}	Low-Level Input Voltage	_		2.3V to 2.7V	_	0.7	_	0.7	V
	Voltago	_		3.0V to 3.6V	_	0.8	_	0.8	
		$I_{OH} = -50\mu A$		1.65V to 3.6V	V _{CC} -0.2	_	V _{CC} -0.3	_	
		I _{OH} = -4mA		1.65V	1.2	_	1.05	_	
\ <i>I</i>	High-Level	I _{OH} = -8mA		2.3V	1.7	_	1.65	_	v
V_{OH}	Output Voltage	101		2.7V	2.2	_	2.05	_	V
		$I_{OH} = -12mA$		3.0V	2.4	_	2.48	_	
		I _{OH} = -24mA		3.0V	2.3	_	2.0	_	
		ow-Level Output $I_{OL} = 100\mu A$ $I_{OL} = 4mA$ $I_{OL} = 8mA$ $I_{OL} = 12mA$		1.65V to 3.6V	_	0.2	_	0.3	
				1.65V	_	0.45	_	0.65	
V_{OL}				2.3V	_	0.60	_	0.80	V
	voltage			2.7V	_	0.40	_	0.60	
		I _{OI} = 24mA		3.0V	_	0.55	_	0.80	
loff	Power Down Leakage Current	V_1 or $V_0 = 0$ or	5.5V	0V	_	±10	_	20	μΑ
l _l	Input Current Control Pins	V _I = GND or 5.	5V	0 to 3.6V	_	±5	_	±20	μΑ
l _{OZ}	Z-State Current Including Input Current I/O Pins	V _I = GND or 5.5V V _O = 0 to 5.5V		3.6V	_	±5	_	±20	μΑ
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$		3.6V	_	10	_	40	μA
Δlcc	Additional Supply Current	One Input at V_{CC} -0.6V $I_O = 0A$		2.7V to 3.6V	_	500	_	5000	μΑ
C.	Input	Control Pins	V GND or V	0V to 3.6V	4.0 T	ypical	4.0 T	ypical	рF
	Capacitance	I/O Pins	$V_I = GND \text{ or } V_{CC}$	0 10 3.0 0	5.5 T	ypical	5.5 T	ypical	PΓ



Switching Characteristics

Symbol	Parameter	Test Conditions	V _{CC}	7	Γ _A = +25°(C		40°C to 5°C		40°C to 25°C	Unit
]	Conditions		Min	Тур	Max	Min	Max	Min	Max	
			1.8V ± 0.15V	5.0	2.5	_	5.0	_	5.5	_	
	Pulse Width	Figure 1	2.5V ± 0.2V	4.0	2.0	_	4.0	_	4.5	_]
t _W	LE	i igure i	2.7V	3.0	1.7	_	3.0	_	3.5	_	ns
			$3.3V \pm 0.3V$	3.0	1.5	_	3.0	_	3.5	_	
			1.8V ± 0.15V	4.0	2.0	_	4.0	_	4.5	_	
	Set-up Time D _N to	Figure 1	$2.5V \pm 0.2V$	3.0	1.5	_	3.0	_	3.5	_]
tsu	LE	Figure 1	2.7V	2.0	1.0	_	2.0	_	2.5	_	ns
			3.3V ± 0.3V	2.0	1.0	_	2.0	_	2.5	_	1
			1.8V ± 0.15V	3.0	1.5	_	3.0	_	3.5	_	
	Hold Time	Figure 4	2.5V ± 0.2V	2.0	1.0	_	2.0	_	2.5	_	1
t _H	D _N to LE	Figure 1	2.7V	1.5	1.0	_	1.5	_	2.0	_	ns
			3.3V ± 0.3V	1.5	1.0	_	1.5	_	2.0	_	1
			1.8V ± 0.15V	1	6	12.2	1	12.7	1	16.9	
	Propagation Delay	F:	2.5V ± 0.2V	1	3.9	7.8	1	8.3	1	8.7	1
t _{PD}	D _N to Q _N	Figure 1	2.7V	1	4.2	7.8	1	8.1	1	9.5	ns
			3.3V ± 0.3V	1.5	3.8	6.8	1.5	7.4	1.5	8	1
			1.8V ± 0.15V	1	7	14.8	1	15.3	1	22.5	
	Propagation Delay	F:	2.5V ± 0.2V	1	4.5	10	1	10.5	1	12.4	ns
t _{PD}	LE to Q _N	Figure 1	2.7V	1	5.4	8.2	1	9.5	1	12	
			3.3V ± 0.3V	1.5	4.4	7.2	1.5	8.5	1.5	11	1
			1.8V ± 0.15V	1	7.8	16.5	1	17	1	18.7	
	Enable Time OE	F:	2.5V ± 0.2V	1	4	9	1	9.5	1	10.3	1
t _{EN}	to Q _N	Figure 1	2.7V	1	4.4	8.3	1	8.5	1	9.5	ns
			3.3V ± 0.3V	1.7	4.1	7.3	1.7	7.5	1.7	9	1
			1.8V ± 0.15V	1	7.8	16.5	1	17	1	18.4	
	Disable Time OE	Figure 4	2.5V ± 0.2V	1	4	9	1	9.5	1	10.5	1
IDIS	t _{DIS} to Q _N	Figure 1	2.7V	1	4.4	8.3	1	8.5	1	9.1	ns
			3.3V ± 0.3V	1.7	4.1	7.3	1.7	7.5	1.7	9	1
			1.8V ± 0.15V	1	7.8	16.5	1	17	1	18.4	
	Disable Time OE	Figure 4	2.5V ± 0.2V	1	4	9	1	9.5	1	10.5]
t _{DIS}	to Q _N	Figure 1	2.7V	1	4.4	8.3	1	8.5	1	9.1	ns
			3.3V ± 0.3V	1.7	4.1	7.3	1.7	7.5	1.7	9	1
tsk(0)	Output Skew Time	_	3.3V ± 0.3V	_	_	1.0	_	_	_	1.5	ns

Operating Characteristics

 $T_A = +25^{\circ}C$

Symbol	Parameter	Test Conditions	V _{CC}	Тур	Unit
	Power Dissipation Capacitance per Gate	£ 10MI	1.8V ± 0.15V	9.9	
C_PD		f = 10MHz Outputs Enabled	2.5V ± 0.2V	10.2	pF
		Outputs Enabled	$3.3V \pm 0.3V$	10.6	



Package Characteristics

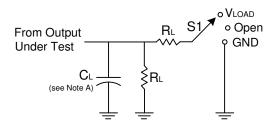
Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
θ_{JA}	Thermal Resistance Junction-to-Ambient	TSSOP-20	(Note 9)	-	74	_	°C/W
θЈС	Thermal Resistance Junction-to-Case	TSSOP-20	(Note 9)	_	15	_	°C/W
θја	Thermal Resistance Junction-to-Ambient	V-QFN4525-20	(Note 9)	_	67	_	°C/W
θ _{JC}	Thermal Resistance Junction-to-Case	V-QFN4525-20	(Note 9)	1	20	_	°C/W

Note:

^{9.} Test conditions for TSSOP-20 and V-QFN4525-20: Devices mounted on 4 layer FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout per JESD 51-7.

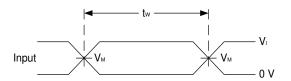


Parameter Measurement Information

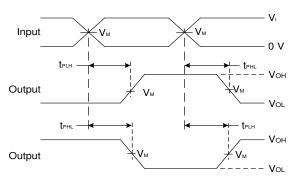


TEST	S1
tplh/tphl	Open
t _{PLZ} /t _{PZL}	V_{LOAD}
t _{PHZ} /t _{PZH}	GND

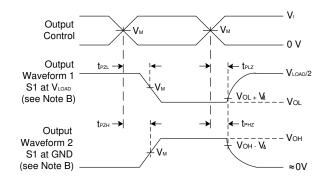
V	Inp	uts	V	V	0	Б		
V _{CC}	VI	t _r /t _f	V _M V _{LOAD}		CL	R_L	$\mathbf{V}\Delta$	
1.8V ± 0.15V	V_{CC}	≤2ns	V _{CC} /2	2 x V _{CC}	30pF	1ΚΩ	0.15V	
2.5V ± 0.2V	V_{CC}	≤2ns	V _{CC} /2	2 x V _{CC}	30pF	500Ω	0.15V	
2.7V	2.7V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V	
$3.3V \pm 0.3V$	2.7V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V	



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

May 2015

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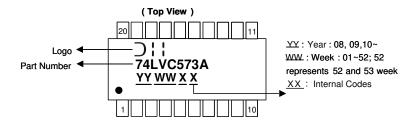
- Notes:
- A. Includes test lead and test apparatus capacitance.
 B. All pulses are supplied at pulse repetition rate ≤ 10MHz.
 C. Inputs are measured separately one transition per measurement.
 - D. t_{PLZ} and t_{PHZ} are the same as t_{DIS} .
 - E. t_{PZL} and t_{PZH} are the same as t_{EN0}
 - F. t_{PLH} and t_{PHL} are the same as $t_{PD.}$

Figure 1 Load Circuit and Voltage Waveforms



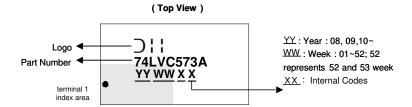
Marking Information

(1) TSSOP-20



Part Number	Package
74LVC573AT20	TSSOP-20

(2) V-QFN4525-20



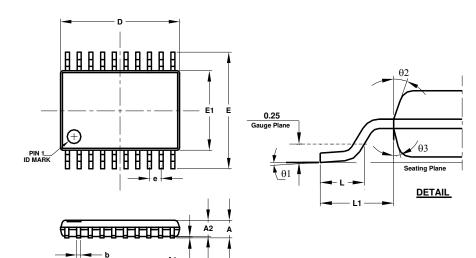
Part Number	Package
74LVC573AQ20	V-QFN4525-20



Package Outline Dimensions

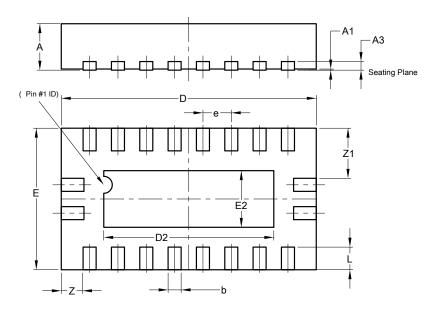
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

(1) Package Type: TSSOP-20



TSSOP-20				
Dim	Min	Max	Тур	
Α	-	1.20	-	
A 1	0.05	0.15	-	
A2	0.80	1.05	1	
b	0.19	0.30	-	
С	0.09	0.20	-	
D	6.40	6.60	6.50	
Е	6.20	6.60	6.40	
E1	4.30	4.50	4.40	
е	0.65 BSC			
L	0.45	0.75	0.60	
L1	1.0 REF			
θ1	0°	8°	-	
θ2	10°	14°	12°	
θ3	10°	14°	12°	
All Dimensions in mm				

(2) Package Type: V-QFN4525-20



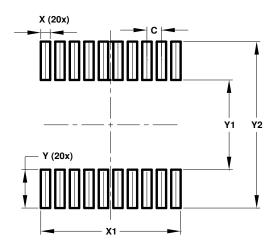
V-QFN4525-20				
Dim	Min	Max	Тур	
Α	0.75	0.85	0.80	
A 1	0.00	0.05	0.02	
А3	-	-	0.15	
b	0.18	0.30	0.23	
D	4.45	4.55	4.50	
D2	2.85	3.15	3.00	
Е	2.45	2.55	2.50	
E2	0.85	1.15	1.00	
е	0.50BSC			
٦	0.30	0.50	0.40	
Z	-	1	0.385	
Z 1	-	-	0.885	
All Dimensions in mm				



Suggested Pad Layout

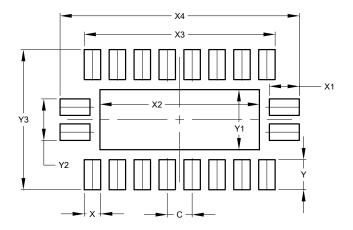
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(1) Package Type: TSSOP-20



Dimensions	Value (in mm)	
С	0.650	
Х	0.420	
X1	6.270	
Υ	1.780	
Y 1	4.160	
Y2	7.720	

(2) Package Type: V-QFN4525-20



Dimensions	Value (in mm)
С	0.500
Х	0.330
X1	0.600
X2	3.200
Х3	3.830
X4	4.800
Υ	0.600
Y1	1.200
Y2	0.830
Y3	2.800



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